L Number	Hits	Search Text	DB	Time stamp
- Number	20	(byoung adj2 ho near3 lim).in.	USPAT; US-PGPUB;	2003/03/08 11:17
_	528	(349/187).CCLS.	EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/08
_	124	(349/192).CCLS.	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/08 11:17
-	33	((((349/187).CCLS.) ((349/192).CCLS.)) and etch\$3 same substrate ) and wet and dry	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/08
_	157	((349/187).CCLS.) and etch\$3 same substrate	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/09 19:40
_	132	((349/187).CCLS.) and substrate same (thin thinner) and etch\$3	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/08 17:14
	1	((216/80).CCLS.) and dry adj2 etch\$3 same (clean cleaning)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/08 17:29
_	8	((216/80).CCLS.) and dry adj2 etch\$3 same substrate and (clean cleaning)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/08
_	43	((216/23).CCLS.) and dry adj2 etch\$3	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/09
-	190	(216/80).CCLS.	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/09 10:54
_	47	etch\$3 RIE CDE half adj ash) and (clean cleaning impurities planarized	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/09 10:57
-	36	etch\$3 RIE CDE half adj ash) same substrate and (clean cleaning impurities	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/09 11:22
_	269	planarized planarization) (349/97).CCLS.	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/09 11:22
-	4	((349/97).CCLS.) and ((dry plasma) adj2 etch\$3 RIE CDE half adj ash)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/09
-	1345	(349/158).CCLS.	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/09
-	61	(349/160).CCLS.	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/03/09 11:30
-	28	((349/160).CCLS.) and etch\$3	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:36

-	185	((349/158).CCLS.) and etch\$3	USPAT;	2003/03/09
			US-PGPUB;	11:46
			EPO; JPO;	
			DERWENT	1
_	38	((349/158).CCLS.) and ((dry plasma) adj2	USPAT;	2003/03/09
		etch\$3 RIE CDE half adj ash)	US-PGPUB;	11:37
			EPO; JPO;	
			DERWENT	
_	145	(((349/158).CCLS.) and etch\$3.) not	USPAT;	2003/03/09
		((((349/158).CCLS.) and ((dry plasma)	US-PGPUB;	19:40
		adj2 etch\$3 RIE CDE half adj ash))	EPO; JPO;	
		(((349/160).CCLS.) and etch\$3)	DERWENT	
		((216/23).CCLS.))		
	180	(((349/187).CCLS.) ((349/192).CCLS.)) and	USPAT;	2003/03/09
	100	etch\$3 same substrate	US-PGPUB;	11:48
		eccity same subscrate	EPO; JPO;	11.40
			DERWENT	
_	28	((349/192).CCLS.) and etch\$3 same	USPAT;	2003/03/09
-	28	substrate	USPAT; US-PGPUB;	11:48
		Substrate		11.40
			EPO; JPO;	
_	288	(429/704) CCI 6	DERWENT USPAT;	2002/02/00
-	200	(438/704).CCLS.		2003/03/09
			US-PGPUB;	13:23
			EPO; JPO;	
			DERWENT	1
-	8	((1-1), 1-1), 1-1-1, (11-1)	USPAT;	2003/03/09
		crystal)	US-PGPUB;	13:24
			EPO; JPO;	
			DERWENT	
-	99	((::::,:::::::::::::::::::::::::::::::	USPAT;	2003/03/09
		adj2 substrate).	US-PGPUB;	13:34
			EPO; JPO;	
			DERWENT	
-	57		USPAT;	2003/03/09
		etch\$3 RIE CDE half adj ash)	US-PGPUB;	15:23
			EPO; JPO;	
			DERWENT	
-	8	5249422.URPN.	USPAT	2003/03/09
				16:33
-	139	(216/23).CCLS.	USPAT;	2003/03/09
			US-PGPUB;	17:06
			EPO; JPO;	
			DERWENT	
-	38	((216/23).CCLS.) and etch\$3 same	USPAT;	2003/03/09
!		substrate and wet and (dry RIE CDE half	US-PGPUB;	17:27
		adj ash plasma)	EPO; JPO;	
			DERWENT	1
_	6	5851411.URPN.	USPAT	2003/03/09
	Ĭ			17:21
_	72	349/\$.ccls. and etch\$3 same substrate and	USPAT;	2003/03/09
	, ,	((dry plasma)adj2 etch\$3 RIE CDE half adj	US-PGPUB;	17:32
]		ash) and (planarize planarization	EPO; JPO;	1 - 7 - 5 -
		planarized cleaning) and (process	DERWENT	
		method).ti.	DELMARIAT	
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